



# **MMBT3904T**

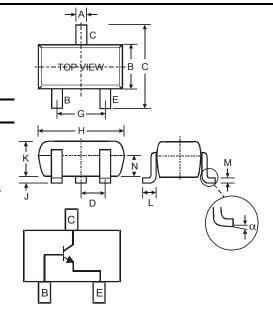
### NPN SMALL SIGNAL SURFACE MOUNT TRANSISTOR

### **Features**

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT3906T)
- Ultra-Small Surface Mount Package
- Lead Free/RoHS Compliant (Note 2)
- "Green" Device (Note 3 and 4)

### **Mechanical Data**

- Case: SOT-523
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: 1N, See Page 3
- Ordering & Date Code Information: See Page 3
- Weight: 0.002 grams (approximate)



SOT-523										
Dim	Min	Max	Тур							
Α	0.15	0.30	0.22							
В	0.75	0.85	0.80							
С	1.45	1.75	1.60							
D		_	0.50							
G	0.90	1.10	1.00							
Н	1.50	1.70	1.60							
J	0.00	0.10	0.05							
K	0.60	0.80	0.75							
L	0.10	0.30	0.22							
М	0.10	0.20	0.12							
N	0.45	0.65	0.50							
α	0°	8°	_							
All D	imens	ions in	mm							

### **Maximum Ratings** @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
Collector-Base Voltage	V <sub>CBO</sub>	60	V		
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V		
Emitter-Base Voltage	$V_{EBO}$	6.0	V		
Collector Current - Continuous	Ic	200	mA		
Power Dissipation (Note 1)	P <sub>d</sub>	150	mW		
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	833	°C/W		
Operating and Storage Temperature Range	T <sub>j</sub> , T <sub>STG</sub>	-55 to +150	°C		

Notes:

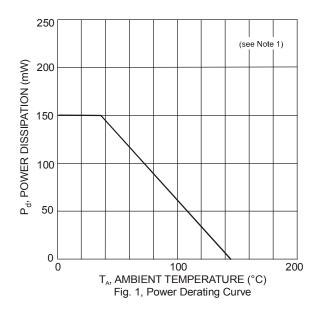
- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead\_free/index.php.
- Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

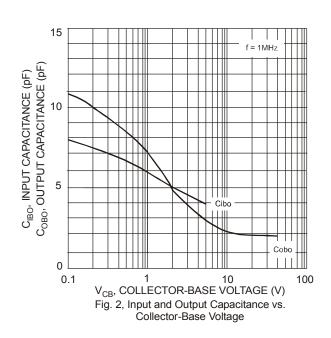


### **Electrical Characteristics** @TA = 25°C unless otherwise specified

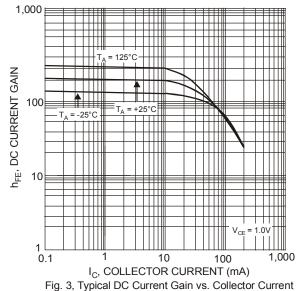
Characteristic	Symbol	Min	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 5)	•		•	•			
Collector-Base Breakdown Voltage	V <sub>(BR)CBO</sub>	60	_	V	$I_C = 10\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	40	_	V	I <sub>C</sub> = 1.0mA, I <sub>B</sub> = 0		
Emitter-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	6.0	_	V	$I_E = 10\mu A, I_C = 0$		
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$		
Base Cutoff Current	I <sub>BL</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3.0V$		
ON CHARACTERISTICS (Note 5)							
DC Current Gain	h <sub>FE</sub>	40 70 100 60 30	300 — —	_	$I_{C} = 100\mu A, V_{CE} = 1.0V$ $I_{C} = 1.0mA, V_{CE} = 1.0V$ $I_{C} = 10mA, V_{CE} = 1.0V$ $I_{C} = 50mA, V_{CE} = 1.0V$ $I_{C} = 100mA, V_{CE} = 1.0V$		
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		0.20 0.30	V	$I_C = 10mA$ , $I_B = 1.0mA$ $I_C = 50mA$ , $I_B = 5.0mA$		
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	0.65	0.85 0.95	V	$I_C = 10$ mA, $I_B = 1.0$ mA $I_C = 50$ mA, $I_B = 5.0$ mA		
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	$C_{obo}$	_	4.0	pF	$V_{CB} = 5.0V$ , $f = 1.0MHz$ , $I_E = 0$		
Input Capacitance	$C_{ibo}$	_	8.0	pF	$V_{EB} = 0.5V$ , $f = 1.0MHz$ , $I_C = 0$		
Input Impedance	h <sub>ie</sub>	1.0	10	kΩ			
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1.0mA,$		
Small Signal Current Gain	h <sub>fe</sub>	100	400	_	f = 1.0kHz		
Output Admittance	h <sub>oe</sub>	1.0	40	μS			
Current Gain-Bandwidth Product	$f_{T}$	300	_	MHz	$V_{CE} = 20V, I_{C} = 10mA,$ f = 100MHz		
Noise Figure	NF	_	5.0	dB	$V_{CE} = 5.0 \text{Vdc}, I_{C} = 100 \mu \text{Adc},$ $R_{S} = 1.0 \text{K}\Omega, f = 1.0 \text{MHz}$		
SWITCHING CHARACTERISTICS							
Delay Time	t <sub>d</sub>	_	35	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$		
Rise Time	t <sub>r</sub>		35	ns	$V_{BE(off)} = -0.5V, I_{B1} = 1.0mA$		
Storage Time	t <sub>s</sub>	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA$		
Fall Time	t <sub>f</sub>	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$		

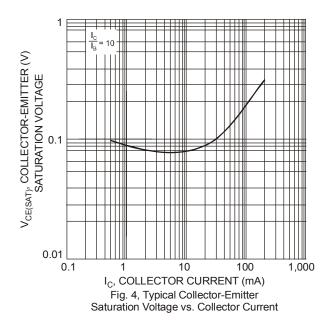
Notes: 5. Short duration pulse test used to minimize self-heating effect.

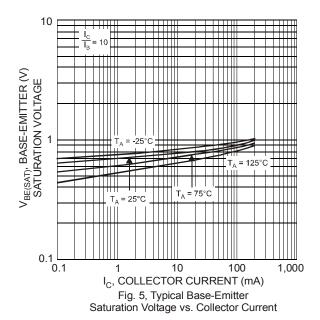










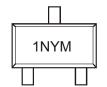


## Ordering Information (Note 6)

Device	Packaging	Shipping			
MMBT3904T-7-F	SOT-523	3000/Tape & Reel			

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

# **Marking Information**



1N = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002) M = Month (ex: 9 = September)

Date Code Key

Year	1998	1999	2000	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	J	K	L	М	N	Р	R	S	Т	U	V	W	Х	Υ	Z
Month	Jan	Fe	b	Mar	Apr	May	Ju	n	Jul	Aug	Sep	Oc	t	Nov	Dec
Code	1	2		3	4	5	6		7	8	9	0		N	D



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